



浙江世菱半导体有限公司  
ZHEJIANG SHILING SEMICONDUCTOR CO.,LTD.

## 产品规格书

### Specification of products

产品名称：快恢复二极管

产品型号：MURP600100

浙江世菱半导体有限公司  
ZHEJIANG SHILING SEMICONDUCTOR CO., LTD.

地址：浙江省 丽水市 莲都区

电话：(0578) 3012571 3615078

传真：(0578) 3611180

邮编：323000

E-mail: smrshiling01@163.com

[Http://www.smrshiling.com](http://www.smrshiling.com)

拟制	审核	核准
林益龙	曹剑龙	宗瑞

## Ultra-Fast Soft Recovery Diode Module

### Description

Ultra-FRD module devices are optimized to reduce losses and EMI/RFI in high frequency power conditioning electrical systems. These diode modules are ideally suited for power converters, motors drives and other applications where switching losses are significant portion of the total losses.

### Features

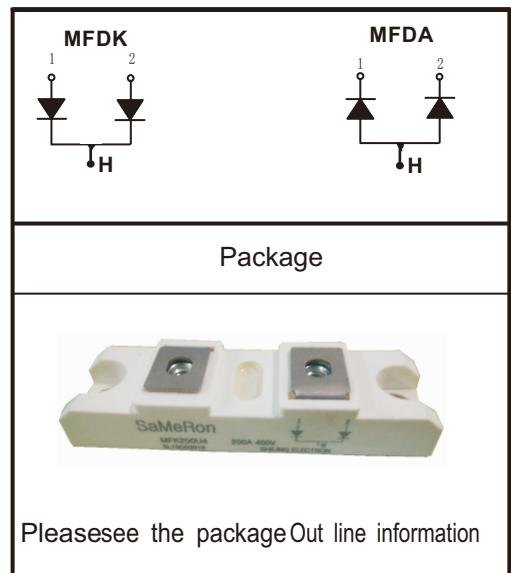
- ☛ Repetitive Reverse Voltage :  $V_{RRM} = 100V$
- ☛ Low Forward Voltage Drop :  $V_F$  (typ.) = 1.0V
- ☛ Average Forward Current :  $I_{F(AV)} = 600A$  @  $T_c = 100^\circ C$
- ☛ Ultra-Fast Reverse Recovery Time :  $t_{rr}$  (typ.) = 100 ns
- ☛ Extensive Characterization of Recovery Parameters
- ☛ Reduced EMI and RFI
- ☛ Non IsolationType Package

### Applications

MotorDrives, Free wheel use, High Power Converters, Welders, Various Switching and Telecommunication Power Supply.

### Equivalent Circuit and Package

Equivalent Circuit



### Absolute Maximum Ratings @ $T_j=25^\circ C$ (Per Leg)

Symbol	Parameter	Conditions	Ratings	Unit
$V_{RRM}$	Repetitive Peak Reverse Voltage		100	V
$V_{R(DC)}$	Reverse DC Voltage		160	V
$I_{F(AV)}$	Average Forward Current @ $T_c = 25^\circ C$ @ $T_c = 100^\circ C$	Resistive Load	600	A
			300	A
$I_{FSM}$	Surge (non-repetitive) Forward Current	One Half Cycle at 60Hz, Peak Value	6000	A
$I_t^2$	$I^2t$ for Fusing	Value for One Cycle Current, $t_w = 8.3ms$ , $T_j = 25^\circ C$ Start	$45.0 \times 10^3$	$A^2 s$
$T_j$	Junction Temperature		-40 ~ 125	$^\circ C$
$T_{sta}$	Storage Temperature		-40 ~ 125	$^\circ C$
$P_d$	Maximum Power Dissipation		700	W
-	Mounting Torque		4.0	N. m
-	Terminal Torque		3.0	N. m

## Rating and Characteristic

### Performance Curves

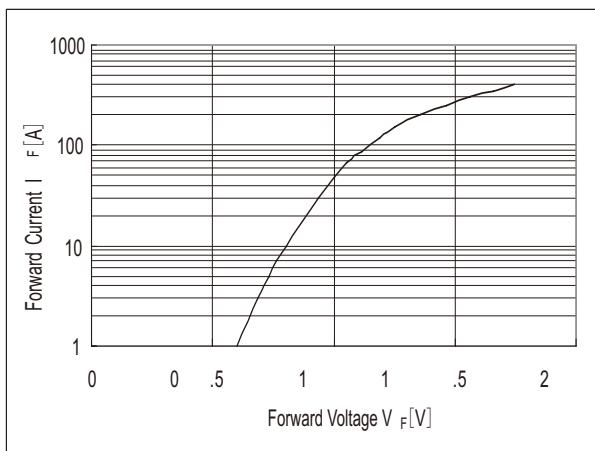


Fig. 1 : Typical Forward Voltage Drop  
vs. Instantaneous Forward Current

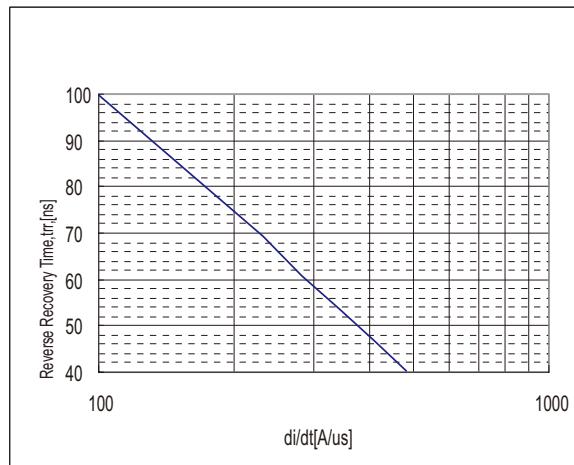


Fig. 2 : Typical Reverse Recovery Time  
vs.  $-di/dt$

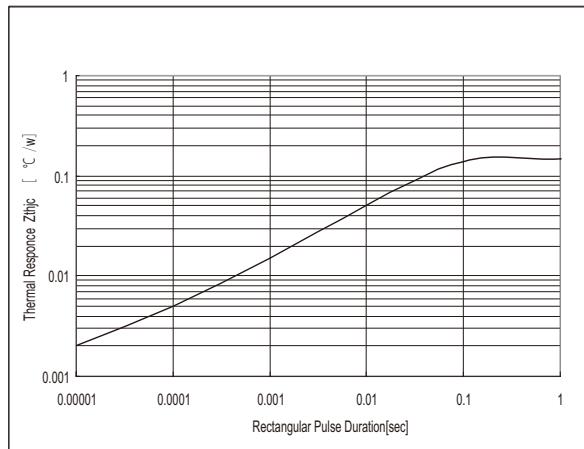


Fig. 3 : Transient Thermal Impedance ( $Z_{thjc}$ )  
Characteristics

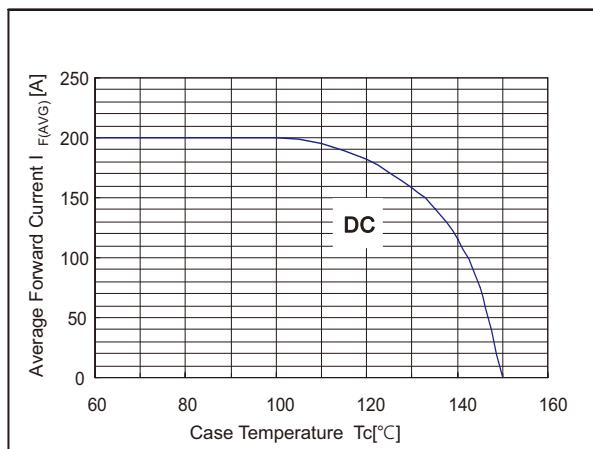


Fig. 4 : Forward Current Derating Curve

## Thermal Characteristics

Symbol	Parameter	Conditions	Values			Unit
			Min.	Typ.	Max.	
$R_{th(j-c)}$	Thermal Resistance	Junction to Case	-	-	0.15	°C/W

## Electrical Characteristics

@ $T_j=25^\circ\text{C}$  (unless otherwise specified)

Symbol	Parameter	Conditions	Values			Unit
			Min.	Typ.	Max.	
$V_R$	Cathode Anode Breakdown Voltage	$I_R= 100\mu\text{A}$	100	-	-	V
$V_{FM}$	Maximum Forward Voltage	$I_{FM}= 200\text{A}, T_c= 25^\circ\text{C}$	-	1.0	1.1	V
		$I_{FM}= 200\text{A}, T_c = 100^\circ\text{C}$	-	0.7	0.8	V
$I_{RRM}$	Repetitive Peak Reverse Current	$T_C= 100^\circ\text{C}, V_{RRM}$ applied	-	-	8.5	mA
$T_{rr}$	Reverse Recovery Time	$I_{FM}= 200\text{A},$ $V_R= 300\text{V}$ $di/dt=-100\text{A/us}$	$T_c= 25^\circ\text{C}$	-	100	ns
			$T_c= 100^\circ\text{C}$	-	180	ns

## Outside Dimension

